

Attorney Docket #10010872-1

Amendments to the Claims

This list of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-11 (Canceled)

12. (currently amended) A semiconductor device, comprising:
a wafer of resistive semiconductor material, having a through hole, a front side, and a back side, the through hole having inner walls, wherein the width of the through hole increases from a minimum width on one side to a maximum width on the other side;
a front contact on the front side of the wafer;
a back contact on the back side of the wafer; and
a metal layer that adheres to the inner walls of the through hole and connects the front contact to the back contact.
13. (Previously presented) The semiconductor device as in claim 12, wherein the through hole is less than 80 microns at its widest.
14. (Previously presented) The semiconductor device as in claim 13, wherein the through hole is less than 50 microns at its widest.
15. (Previously presented) The semiconductor device as in claim 13 wherein the metal layer on the through hole is at least 1000 Angstroms thick where the through hole is the narrowest.
16. (Previously presented) The semiconductor device as in claim 15, wherein the metal layer is selected from the group consisting of NiChrome and gold.

Attorney Docket #10010872-1

17. (Previously presented) The semiconductor device as in claim 15, wherein the metal layer on the through hole is partially plated.

18-20. (canceled)

21. (currently amended) The semiconductor device as in claim 13, wherein [the slope of the walls of the through hole is not constant] the inner walls of the through hole do not have a constant slope.

22. (currently amended) The semiconductor device as in claim 13, wherein the inner walls of the through hole are curved.